

THE SPECIFICATION OF AlGaInP RCLED CHIP

“YL-PSC650nm-1.2mW”

1. DESCRIPTION

This is a AlGaInP RCLED chip. It is P-side up. The peak wavelength is 650 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25°C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (Vf) IF=20mA		2.2		V
Reverse Current (Ir) Vr=3V			10	uA
Radiated Power ¹⁾ (Po) IF=20mA		1.2		mW
Peak Wavelength (λ_p) IF=20mA		650		nm
Spectral Radiation Bandwidth ($\Delta \lambda$) IF=20mA		8		nm
Cut Off Frequency (Fc) 20 + 10mA _{p-p}		75		MHz

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current : 30 mA(DC)
 Reverse Voltage : 3 V(IR=10 μ A)

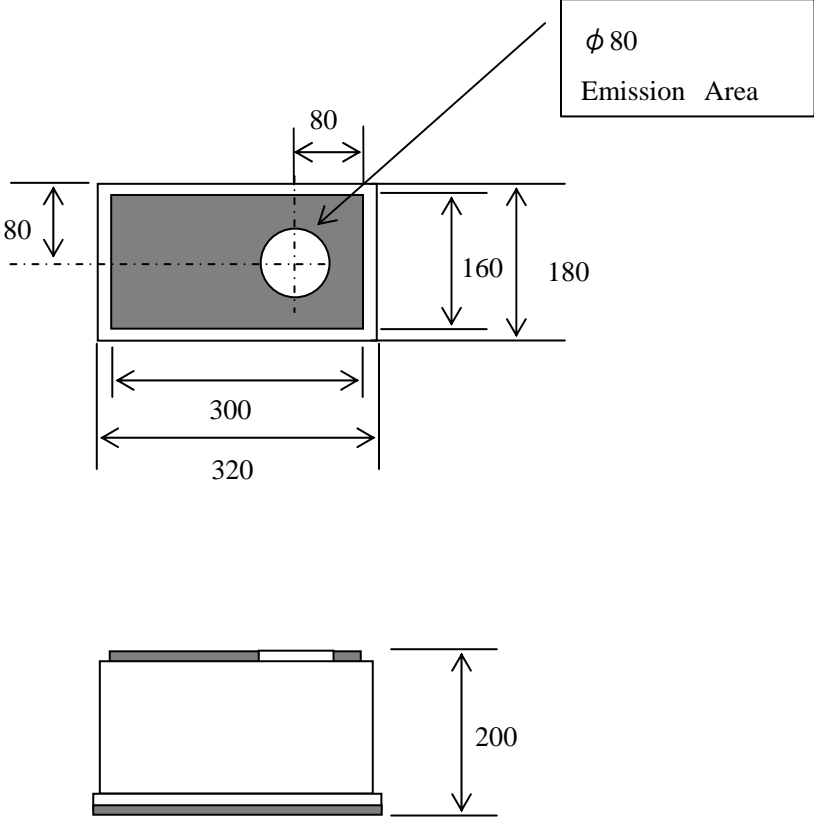
4. PHYSICAL CHARACTERISTICS AND STRUCTURE

- 1) Material : AlGaInP
- 2) Structure : Resonant Cavity Structure
- 3) Die size : 0.180mm \times 0.320mm
- 4) Thickness : 0.200mm
- 5) Emission area : 0.080mm diameter
- 6) Anode Metallization : Gold Alloy
- 7) Cathode Metallization: Gold Alloy

Physical Dimensions

Model YL-PSC650nM-1.2mW

UNIT:um



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.